

SiC Schottky Barrier Diode

V_R	650V
l _F	10A
Q_C	24nC

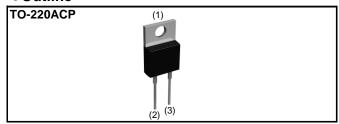
Features

- 1) Shorter recovery time
- 2) Reduced temperature dependence
- 3) High-speed switching possible
- 4) High surge current capability

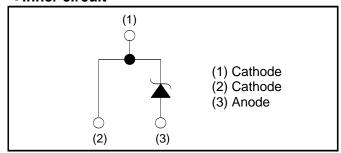
Construction

Silicon carbide epitaxial planar type

Outline



•Inner circuit



Packaging specifications

	Packaging	Tube
	Reel size (mm)	-
Typo	Tape width (mm)	-
Туре	Basic ordering unit (pcs)	50
	Packing code	C9
	Marking	SCS310AP

● Absolute maximum ratings (T_i = 25°C)

Parameter		Symbol	Value	Unit
Reverse voltage (re	petitive peak)	V_{RM}	650	V
Reverse voltage (D	C)	V _R	650	V
Continuous forward	current (T _c = 135°C)	I _F	10	А
Surge non-	PW=10ms sinusoidal, T _j =25°C		82	А
repetitive forward	PW=10ms sinusoidal, T _j =150°C	I _{FSM}	69	А
current	PW=10μs square, T _j =25°C		430	А
Repetitive peak forward current		I _{FRM}	54 * ¹	А
1≦PW≦10ms, T _j =25°C		$\int i^2 dt$	33	A ² s
i ² t value	1≦PW≦10ms, T _j =150°C	J i-at	23	A ² s
Total power disspation		P_{D}	71 * ²	W
Junction temperature		Tj	175	°C
Range of storage temperature		T _{stg}	-55 to +175	°C

^{*1} T_c=100°C, T_i=150°C, Duty cycle=10% *2 T_c=25°C

●Electrical characteristics (T_j = 25°C)

Parameter	Symbol	Conditions	Values			Linit
			Min.	Тур.	Max.	Unit
DC blocking voltage	V_{DC}	I _R =50μA	650	-	-	V
	V _F	I _F =10A, T _j =25°C	-	1.35	1.50	V
Forward voltage		I _F =10A, T _j =150°C	-	1.44	1.71	V
		I _F =10A, T _j =175°C	-	1.50	-	V
Reverse current	I _R	V _R =650V, T _j =25°C	-	0.03	50	μΑ
		V _R =650V, T _j =150°C	-	2	200	μΑ
		V _R =650V, T _j =175°C	-	6	-	μΑ
Total capacitance	С	V _R =1V, f=1MHz	-	500	-	pF
		V _R =650V, f=1MHz	-	46	-	pF
Total capacitive charge	Q_{C}	V _R =400V, di/dt=350A/μs	-	24	-	nC
Switching time	t _C	V _R =400V, di/dt=350A/μs	-	15	-	ns
Non-repetetive Avaranche Energy	E _{ava}	L=1mH	-	130	-	mJ

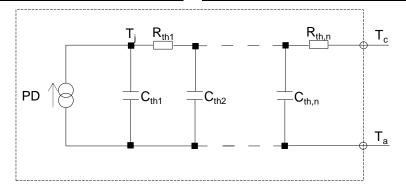
Thermal characteristics

Parameter	Symbol	Conditions	Values			Linit
			Min.	Тур.	Max.	Unit
Thermal resistance	$R_{\text{th(j-c)}}$	-	-	1.5	2.1	°C/W

● Typical Transient Thermal Characteristics

Symbol	Value	Unit
R _{th1}	1.55E-02	
R _{th2}	1.46E-01	K/W
R _{th3}	1.32E+00	

Symbol	Value	Unit
C_{th1}	2.63E-04	
C_{th2}	1.00E-03	Ws/K
C _{th3}	2.13E-03	



•Electrical characteristic curves

Fig.1 V_F - I_F Characteristics

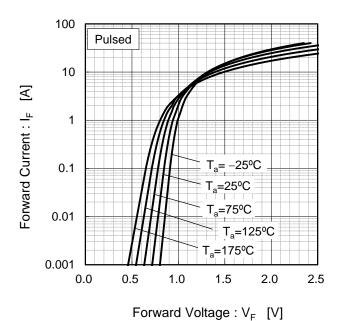
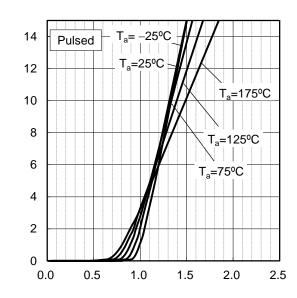


Fig.2 V_F - I_F Characteristics

Forward Current : IF [A]



Forward Voltage : V_F [V]

Fig.3 V_R - I_R Characteristics

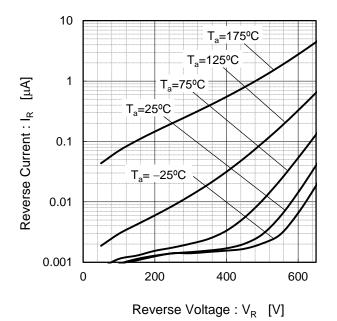
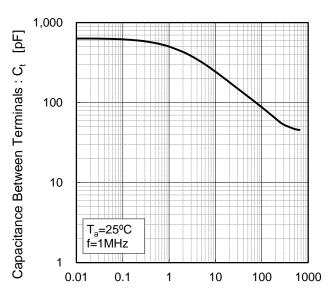


Fig.4 V_R-C_t Characteristics



Reverse Voltage : V_R [V]

•Electrical characteristic curves

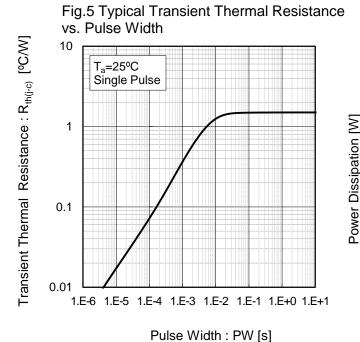
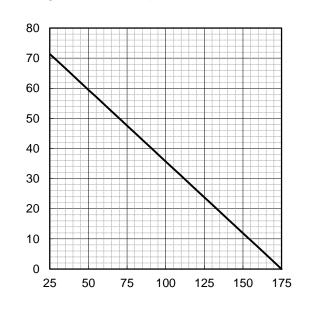
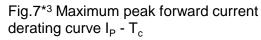


Fig.6 Power Dissipation



Case Temperature : T_c [°C]



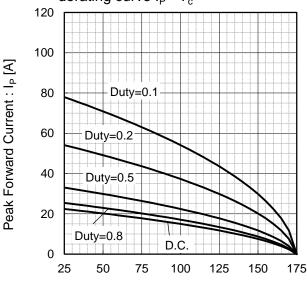
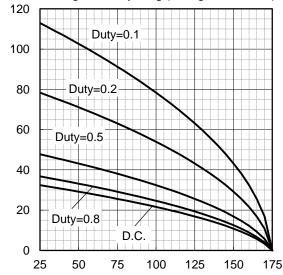


Fig.8*4 Typical peak forward current derating curve I_P - T_c (Not guaranteed)



Case Temperature : T_c [°C]

*3 Based on max Vf, max R_{th(j-c)} Valid for switching of above 10kHz, excluding D.C. curve.

Case Temperature : T_c [°C]

*4 Based on typ Vf, typ R_{th(j-c)} Typical value, not guaranteed Valid for switching of above 10kHz,

excluding D.C. curve

Peak Forward Current : Ip [A]

•Electrical characteristic curves

Fig. 9 Surge non-repetitive forward current vs. Pulse width (Sinusoidal waveform)

1000

T_a=25°C
Single Pulse

10

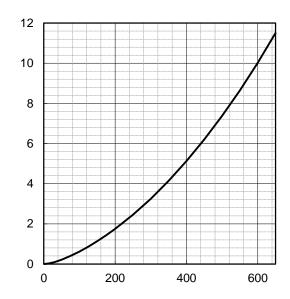
1.E-5

1.E-4

1.E-3

1.E-2

Fig.10 Typical capacitance store energy



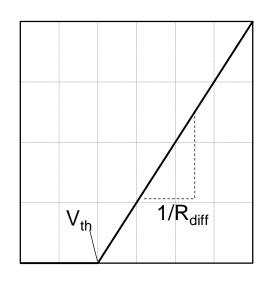
Capacitance stored energy : $E_C[\mu J]$

Reverse Voltage : V_R [V]

Symplified forward characteristic model

Fig.11 Equivalent forward current curve

Pulse Width: PW [s]



Forward Voltage: V_F

$$V_F = V_{th} + R_{diff} I_F$$

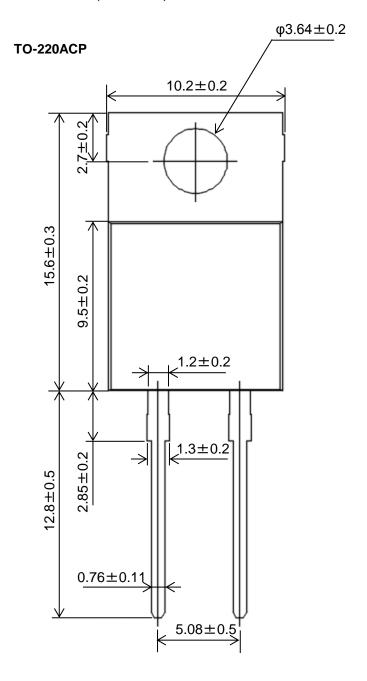
$$\begin{aligned} &V_{th}\left(T_{j}\right) = a_{0} + a_{1} T_{j} \\ &R_{diff}\left(T_{j}\right) = b_{0} + b_{1} T_{j} + b_{2} T_{j}^{2} \end{aligned}$$

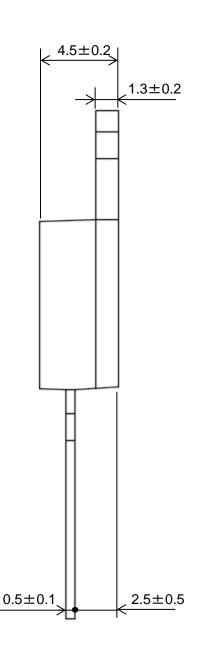
Symbol	Typical Value	Unit
a ₀	9.66E-01	V
a ₁	-1.10E-03	V/°C
b ₀	3.52E-02	Ω
b ₁	7.46E-05	Ω/°C
b ₂	7.68E-07	Ω /°C ²

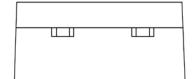
 T_{j} in °C; -55 °C < T_{j} < °C ; I_{F} < 20 A

Forward Current: IF

●Dimensions (Unit: mm)







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